

# HETERO JUNCTION FIELD EFFECT TRANSISTOR NE3503M04

# C TO Ku BAND SUPER LOW NOISE AND HIGH-GAIN AMPLIFIER N-CHANNEL HJ-FET

#### **FEATURES**

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• Super low noise figure and high associated gain NF = 0.45 dB TYP.,  $G_a$  = 12.0 dB TYP. @  $V_{DS}$  = 2 V,  $I_D$  = 10 mA, f = 12 GHz

- · Flat-lead 4-pin thin-type super minimold (M04) package
- Gate width:  $W_g = 160 \mu m$

#### **APPLICATIONS**

- · DBS LNB gain-stage, Mix-stage
- · Low noise amplifier for microwave communication system

#### ORDERING INFORMATION

Part Number	Order Number	Package	Quantity	Marking	Supplying Form
NE3503M04	NE3503M04-A	Flat-lead 4-pin thin-	50 pcs (Non reel)	V75	8 mm wide embossed taping
NE3503M04-T2	NE3503M04-T2-A	type super minimold (M04) (Pb-Free)	3 kpcs/reel		<ul> <li>Pin 1 (Source), Pin 2 (Drain) face the perforation side of the tape</li> </ul>
NE3503M04-T2B	NE3503M04-T2B-A	(IVIO4) (FD-FIEE)	15 kpcs/reel		the perioration side of the tape

Remark To order evaluation samples, contact your nearby sales office.

Part number for sample order: NE3503M04-A

#### ABSOLUTE MAXIMUM RATINGS (TA = +25°C)

Parameter	Symbol	Ratings	Unit
Drain to Source Voltage	V <sub>DS</sub>	4.0	V
Gate to Source Voltage	Vgs	-3.0	V
Drain Current	lσ	Ioss	mA
Gate Current	lg	80	μΑ
Total Power Dissipation	Ptot	125	mW
Channel Temperature	Tch	+125	°C
Storage Temperature	Tstg	-65 to +125	°C

Caution: Observe precautions when handling because these devices are sensitive to electrostatic discharge

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.

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The mark <R> shows major revised points.

The revised points can be easily searched by copying an "<R>" in the PDF file and specifying it in the "Find what:" field.

Parameter

Gate to Source Leak Current

Gate to Source Cutoff Voltage

Saturated Drain Current

Transconductance

Noise Figure

Associated Gain

Unit

μΑ

mΑ

V

mS

dΒ

dΒ

TYP.

0.5

40

-0.7

55

0.45

12.0

MAX.

10

70

-1.5

\_

0.65

MIN.

\_

25

-0.2

40

11.0

### RECOMMENDED OPERATING CONDITIONS ( $T_A = +25$ °C)

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Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Drain to Source Voltage	V <sub>DS</sub>	1	2	3	V
Drain Current	lо	5	10	15	mA
Input Power	Pin	ı	_	0	dBm

Symbol

Igso

IDSS

VGS (off)

gт

NF

 $G_{\mathsf{a}}$ 

## ELECTRICAL CHARACTERISTICS (TA = +25°C, unless otherwise specified)

 $V_{GS} = -3.0 \text{ V}$ 

 $V_{DS} = 2 V$ ,  $V_{GS} = 0 V$ 

 $V_{DS} = 2 \text{ V}, \text{ ID} = 100 \ \mu\text{A}$ 

 $V_{DS} = 2 V$ ,  $I_D = 10 mA$ 

 $V_{DS} = 2 V$ ,  $I_D = 10 \text{ mA}$ , f = 12 GHz

**Test Conditions** 

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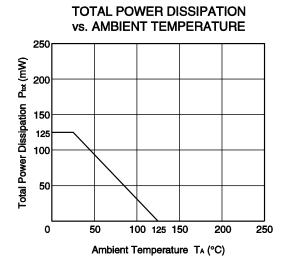
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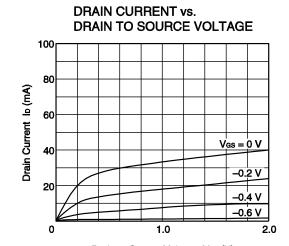
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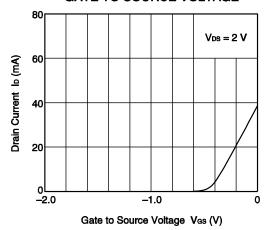
2

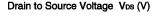
## TYPICAL CHARACTERISTICS (TA = +25°C, unless otherwise specified)



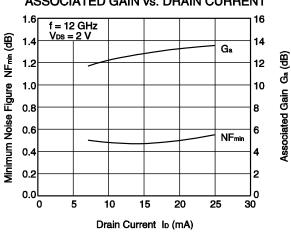


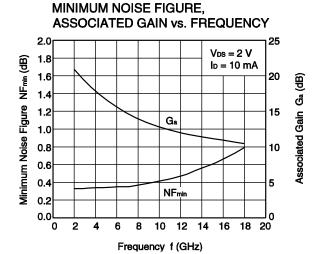
# DRAIN CURRENT vs. GATE TO SOURCE VOLTAGE





#### MINIMUM NOISE FIGURE, ASSOCIATED GAIN vs. DRAIN CURRENT





Remark The graphs indicate nominal characteristics.

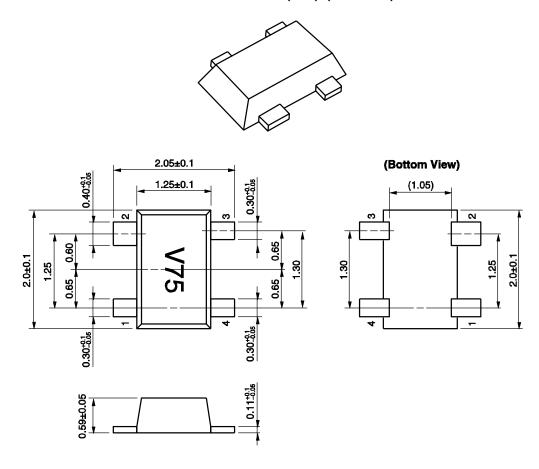
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#### **S-PARAMETERS**

- S-parameters and noise parameters are provided on our Web site in a format (S2P) that enables the direct import of the parameters to microwave circuit simulators without the need for keyboard inputs.
- · Click here to download S-parameters.
- [RF and Microwave] ® [Device Parameters]
- URL http://www.necel.com/microwave/en/

#### **PACKAGE DIMENSIONS**

# FLAT-LEAD 4-PIN THIN-TYPE SUPER MINIMOLD (M04) (UNIT: mm)



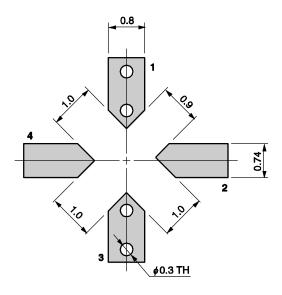
#### **PIN CONNECTIONS**

- 1. Source
- 2. Drain
- 3. Source
- 4. Gate

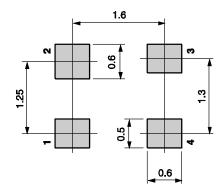
#### MOUNTING PAD DIMENSIONS

# FLAT-LEAD 4-PIN THIN-TYPE SUPER MINIMOLD (M04) (UNIT: mm)

#### -Reference 1-



#### -Reference 2-



#### RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions	Condition Symbol	
Infrared Reflow	Peak temperature (package surface temperature) Time at peak temperature Time at temperature of 220°C or higher Preheating time at 120 to 180°C Maximum number of reflow processes Maximum chlorine content of rosin flux (% mass)	: 260°C or below : 10 seconds or less : 60 seconds or less : 120±30 seconds : 3 times : 0.2%(Wt.) or below	IR260
Partial Heating	Peak temperature (pin temperature) Soldering time (per side of device) Maximum chlorine content of rosin flux (% mass)	: 350°C or below : 3 seconds or less : 0.2%(Wt.) or below	HS350

Caution Do not use different soldering methods together (except for partial heating).

#### Caution

GaAs Products

This product uses gallium arsenide (GaAs).

GaAs vapor and powder are hazardous to human health if inhaled or ingested, so please observe the following points.

- Follow related laws and ordinances when disposing of the product. If there are no applicable laws and/or ordinances, dispose of the product as recommended below.
- Commission a disposal company able to (with a license to) collect, transport and dispose of materials that contain arsenic and other such industrial waste materials.
- 2. Exclude the product from general industrial waste and household garbage, and ensure that the product is controlled (as industrial waste subject to special control) up until final disposal.
- Do not burn, destroy, cut, crush, or chemically dissolve the product.
- Do not lick the product or in any way allow it to enter the mouth.